

Inverting Octal 3-STATE Buffer

MM74HC240

General Description

The MM74HC240 3–STATE buffer utilizes advanced silicon–gate CMOS technology. It possesses high drive current outputs which enable high speed operation even when driving large bus capacitances. These circuits achieve speeds comparable to low power Schottky devices, while retaining the advantage of CMOS circuitry, i.e., high noise immunity and low power consumption. It has a fanout of 15 LS–TTL equivalent inputs.

The MM74HC240 is an inverting buffer and has two active LOW enables ($1\overline{G}$ and $2\overline{G}$). Each enable independently controls 4 buffers.

All inputs are protected from damage due to static discharge by diodes to V_{CC} and ground.

Features

- Typical Propagation Delay: 12 ns
- 3-STATE Outputs for Connection to System Buses
- Wide Power Supply Range: 2-6 V
- Low Quiescent Supply Current: 160 µA (74 Series)
- Output Current: 6 mA
- These are Pb-Free Devices

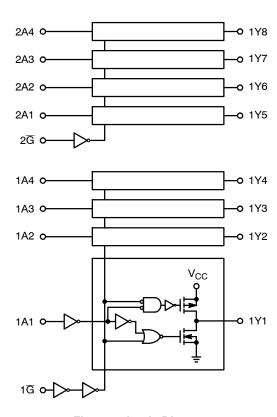


Figure 1. Logic Diagram

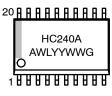


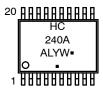


SOIC-20 WB CASE 751D-05

TSSOP-20 WB CASE 948E

MARKING DIAGRAMS





(SOIC-20 WB)

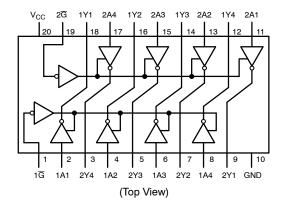
(TSSOP-20 WB)

HC240A = Specific Device Code A = Assembly Location

L/WL = Wafer Lot
Y/YY = Year
W/WW = Work Week
or G = Pb-Free Package

(Note: Microdot may be in either location)

CONNECTION DIAGRAM



TRUTH TABLE

| 1 G | 1A | 1Y | 2 G | 2A | 2Y |
|----------------|----|----|----------------|----|----|
| L | L | Н | L | L | Н |
| L | Н | Н | L | Н | Н |
| Н | L | Z | Н | L | Z |
| Н | Н | Z | Н | Н | Z |

H = HIGH Level

L = LOW Level

Z = HIGH Impedance

ORDERING INFORMATION

See detailed ordering, marking and shipping information in the package dimensions section on page 4 of this data sheet.

MM74HC240

MAXIMUM RATINGS (Note 1)

| Symbol | Parameter | Value | Unit |
|-----------------------------------|---|-------------------------------|------|
| V _{CC} | Supply Voltage | −0.5 to +7.0 | V |
| V _{IN} | DC Input Voltage | -0.5 to V _{CC} + 0.5 | V |
| V _{OUT} | DC Output Voltage | -0.5 to V _{CC} + 0.5 | V |
| I _{IK} , I _{OK} | Clamp Diode Current | ±20 | mA |
| I _{OUT} | DC Output Current, per Pin | ±35 | mA |
| I _{CC} | DC VCC or GND Current, per Pin | ±70 | mA |
| T _{STG} | Storage Temperature Range | −65 to +150 | °C |
| P _D | Power Dissipation (Note 2) S. O. Package Only | 600 500 | mW |
| T_L | Lead Temperature (Soldering 10 seconds) | 260 | °C |

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- Unless otherwise specified all voltages are referenced to ground.
 Power Dissipation temperature derating plastic "N" package: 12 mW/°C from 65°C to 85°C.

RECOMMENDED OPERATIONG CONDITIONS (Note 1)

| Symbol | Parameter | Min | Max | Unit |
|------------------------------------|---|-------------|--------------------|------|
| V _{CC} | Supply Voltage | 2 | 6 | V |
| V _{IN} , V _{OUT} | DC Input or Output Voltage | 0 | V _{CC} | V |
| T _A | Operating Temperature Range | -55 | +125 | °C |
| t _r , t _f | Input Rise or Fall Times V _{CC} = 2.0 V V _{CC} = 4.5 V V _{CC} = 6.0 V | - - - | 1000 500 400 | ns |

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

DC ELECTRICAL CHARACTERISTICS (Note 3)

| | | | V _{CC} | T _A = | 25°C | $-40^{\circ}\text{C} \le \text{T}_{\text{A}} \le 85^{\circ}\text{C}$ | -55°C ≤ T _A ≤ 125°C | |
|-----------------|--------------------------------------|--|-------------------|-------------------|--------------------|--|--------------------------------|------|
| Symbol | Parameter | Conditions | (V) | Тур | | Guaranteed Li | mits | Unit |
| V _{IH} | Minimum HIGH Level Input Voltage | | 2.0 4.5 6.0 | - - - | 1.5 3.15 4.2 | 1.5 3.15 4.2 | 1.5 3.15 4.2 | ٧ |
| V _{IL} | Maximum LOW Level Input Voltage | | 2.0 4.5 6.0 | - - - | 0.5 1.35 1.8 | 0.5 1.35 1.8 | 0.5 1.35 1.8 | V |
| V _{OH} | Minimum HIGH Level Output Voltage | $V_{IN} = V_{IH} \text{ or } V_{IL}$ $ I_{OUT} \le 20 \ \mu\text{A}$ | 2.0 4.5 6.0 | 2.0 4.5 6.0 | 1.9 4.4 5.9 | 1.9 4.4 5.9 | 1.9 4.4 5.9 | V |
| | | $V_{IN} = V_{IH} \text{ or } V_{IL}$ $ I_{OUT} \le 6.0 \text{ mA}$ $ I_{OUT} \le 7.8 \text{ mA}$ | 4.5 6.0 | 4.2 5.7 | 3.98 5.48 | 3.84 5.34 | 3.7 5.2 | V |
| V _{OL} | Maximum LOW Level Output Voltage | $V_{IN} = V_{IH} \text{ or } V_{IL}$ $ I_{OUT} \le 20 \mu\text{A}$ | 2.0 4.5 6.0 | 0 0 0 | 0.1 0.1 0.1 | 0.1 0.1 0.1 | 0.1 0.1 0.1 | V |
| | | $V_{IN} = V_{IH} \text{ or } V_{IL}$ $ I_{OUT} \le 6.0 \text{ mA}$ $ I_{OUT} \le 7.8 \text{ mA}$ | 4.5 6.0 | 0.2 0.2 | 0.26 0.26 | 0.33 0.33 | 0.4 0.4 | V |
| I _{IN} | Maximum Input Current | V _{IN} = V _{CC} or GND | 6.0 | - | ±0.1 | ±1.0 | ±1.0 | μА |

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DC ELECTRICAL CHARACTERISTICS (Note 3) (continued)

| | | | V _{cc} | T _A = | 25°C | $-40^{\circ}\text{C} \le \text{T}_{\text{A}} \le 85^{\circ}\text{C}$ | -55°C ≤ T _A ≤ 125°C | |
|-----------------|--|---|-----------------|------------------|------|--|--------------------------------|------|
| Symbol | Parameter | Conditions | (V) | Тур | | Guaranteed Li | mits | Unit |
| l _{OZ} | Maximum 3-STATE Output Leakage Current | $\begin{aligned} &V_{IN} = V_{IH} \text{ or } V_{IL} \\ &V_{OUT} = V_{CC} \text{ or GND} \\ &\overline{G} = V_{IH}, \ G = V_{IL} \end{aligned}$ | 6.0 | - | ±0.5 | ±5 | ±10 | μΑ |
| I _{CC} | Maximum Quiescent Supply Current | $V_{IN} = V_{CC}$ or GND $I_{OUT} = 0 \mu A$ | 6.0 | - | 8.0 | 80 | 160 | μΑ |

^{3.} For a power supply of 5 V $\pm 10\%$ the worst case output voltages (V_{OH}, and V_{OL}) occur for HC at 4.5 V. Thus the 4.5 V values should be used when designing with this supply. Worst case V_{IH} and V_{IL} occur at V_{CC} = 5.5 V and 4.5 V respectively. (The V_{IH} value at 5.5 V is 3.85 V.) The worst case leakage current (I_{IN}, I_{CC}, and I_{OZ}) occur for CMOS at the higher voltage and so the 6.0 V values should be used.

AC ELECTRICAL CHARACTERISTICS

| Symbol | Parameter | Conditions | Тур | Guaranteed Limit | Unit |
|-------------------------------------|--|--|-----|---------------------|------|
| t _{PHL} , t _{PLH} | Maximum Propagation Delay | C _L = 45 pF | 12 | 18 | ns |
| t _{PZH} , t _{PZL} | Maximum Enable Delay to Active Output | R_L = 1 kΩ, C_L = 45 pF | 14 | 28 | ns |
| t _{PHZ} , t _{PLZ} | Maximum Disable Delay from Active Output | $R_L = 1 \text{ k}\Omega$, $C_L = 5 \text{ pF}$ | 13 | 25 | ns |

AC ELECTRICAL CHARACTERISTICS ($V_{CC} = 2.0 \text{ V}$ to 6.0 V, $C_L = 50 \text{ pF}$, $t_r = t_f = 6 \text{ ns}$ (unless otherwise specified))

| | | | V _{CC} | T _A = | 25°C | $-40^{\circ}\text{C} \le \text{T}_{\text{A}} \le 85^{\circ}\text{C}$ | -55°C ≤ T _A ≤ 125°C | |
|--|--|--|-------------------|------------------|-----------------|--|--------------------------------|------|
| Symbol | Parameter | Conditions | (V) | Тур | | Guaranteed Limits | | Unit |
| t _{PHL} , t _{PLH} | Maximum Propagation Delay | C _L = 50 pF C _L = 150 pF | 2.0 2.0 | 55 80 | 100 150 | 126 190 | 149 224 | ns |
| | | C _L = 50 pF C _L = 150 pF | 4.5 4.5 | 12 22 | 20 30 | 25 38 | 30 45 | ns |
| | | C _L = 50 pF C _L = 150 pF | 6.0 6.0 | 11 28 | 17 26 | 21 32 | 25 38 | ns |
| t _{PZH} , t _{PZL} | Maximum Output Enable Time | $R_L = 1 \text{ k}\Omega$ $C_L = 50 \text{ pF}$ $C_L = 150 \text{ pF}$ | 2.0 2.0 | 75 100 | 150 200 | 189 252 | 224 298 | ns |
| | | C _L = 50 pF C _L = 150 pF | 4.5 4.5 | 15 20 | 30 40 | 38 50 | 45 60 | ns |
| | | C _L = 50 pF C _L = 150 pF | 6.0 6.0 | 13 17 | 26 34 | 32 43 | 38 51 | ns |
| t _{PHZ} , t _{PLZ} | Maximum Output Disable Time | $R_L = 1 \text{ k}\Omega$ $C_L = 50 \text{ pF}$ | 2.0 4.5 6.0 | 75 15 13 | 150 30 26 | 189 38 32 | 224 45 38 | ns |
| t _{TLH} , t _{THL} | Maximum Output Rise and Fall Time | | 2.0 4.5 6.0 | - - - | 60 12 10 | 75 15 13 | 90 18 15 | ns |
| C _{PD} | Power Dissipation Capacitance (Note 4) | (per buffer) $\overline{G} = V_{IH}$ $\overline{G} = V_{IL}$ | - - | 12 50 | - - | - - | - - | pF |
| C _{IN} | Maximum Input Capacitance | | - | 5 | 10 | 10 | 10 | pF |
| C _{OUT} | Maximum Output Capacitance | | - | 10 | 20 | 20 | 20 | pF |

^{4.} C_{PD} determines the no load dynamic power consumption, $P_D = C_{PD} \cdot V_{CC}^2 \cdot f + I_{CC} \cdot V_{CC}$, and the no load dynamic current consumption, $I_S = C_{PD} \cdot V_{CC} \cdot f + I_{CC}$.

MM74HC240

ORDERING INFORMATION

| Device | Package | Shipping [†] |
|---------------|--------------------------|--------------------------|
| MM74HC240WM | SOIC-20 WB (Pb-Free) | 38 Units / Tube |
| MM74HC240WMX | SOIC-20 WB (Pb-Free) | 1000 Units / Tape & Reel |
| MM74HC240MTCX | TSSOP-20 WB (Pb-Free) | 2500 Units / Tape & Reel |

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

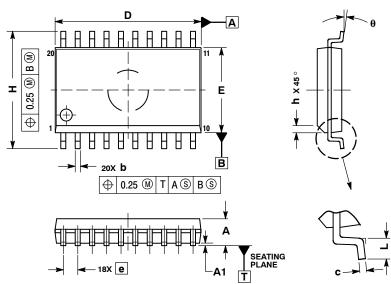




SOIC-20 WB CASE 751D-05 **ISSUE H**

DATE 22 APR 2015

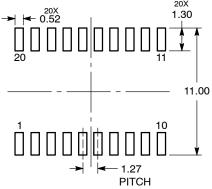
SCALE 1:1



- DIMENSIONS ARE IN MILLIMETERS.
 INTERPRET DIMENSIONS AND TOLERANCES.
- PER ASME Y14.5M, 1994.
 3. DIMENSIONS D AND E DO NOT INCLUDE MOLD
- PROTRUSION.
 MAXIMUM MOLD PROTRUSION 0.15 PER SIDE.
- DIMENSION B DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.13 TOTAL IN EXCESS OF B DIMENSION AT MAXIMUM MATERIAL

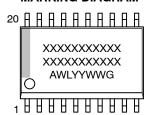
| | MILLIMETERS | | | | |
|-----|-------------|-------|--|--|--|
| DIM | MIN | MAX | | | |
| Α | 2.35 | 2.65 | | | |
| A1 | 0.10 | 0.25 | | | |
| b | 0.35 | 0.49 | | | |
| С | 0.23 | 0.32 | | | |
| D | 12.65 | 12.95 | | | |
| E | 7.40 | 7.60 | | | |
| е | 1.27 | BSC | | | |
| Н | 10.05 | 10.55 | | | |
| h | 0.25 | 0.75 | | | |
| L | 0.50 | 0.90 | | | |
| A | 0 ° | 7 ° | | | |

RECOMMENDED SOLDERING FOOTPRINT*



DIMENSIONS: MILLIMETERS

GENERIC MARKING DIAGRAM*



XXXXX = Specific Device Code = Assembly Location

WL = Wafer Lot ΥY = Year WW = Work Week = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

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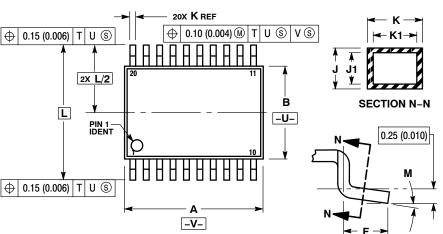
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^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.



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DATE 17 FEB 2016





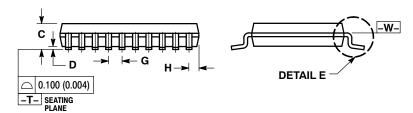
DETAIL E

NOTES:

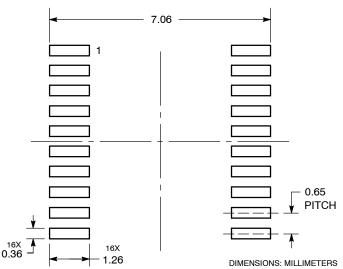
- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: MILLIMETER.
- 3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.
- FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K
- (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.
- TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.

 7. DIMENSION A AND B ARE TO BE
- DETERMINED AT DATUM PLANE -W-

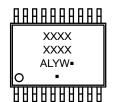
| | MILLIN | IETERS | INC | HES | |
|-----|--------|----------|-----------|-------|--|
| DIM | MIN | MAX | MIN | MAX | |
| Α | 6.40 | 6.60 | 0.252 | 0.260 | |
| В | 4.30 | 4.50 | 0.169 | 0.177 | |
| C | | 1.20 | | 0.047 | |
| D | 0.05 | 0.15 | 0.002 | 0.006 | |
| F | 0.50 | 0.75 | 0.020 | 0.030 | |
| G | 0.65 | BSC | 0.026 BSC | | |
| Н | 0.27 | 0.37 | 0.011 | 0.015 | |
| J | 0.09 | 0.20 | 0.004 | 0.008 | |
| J1 | 0.09 | 0.16 | 0.004 | 0.006 | |
| K | 0.19 | 0.30 | 0.007 | 0.012 | |
| K1 | 0.19 | 0.25 | 0.007 | 0.010 | |
| L | 6.40 | 6.40 BSC | | BSC | |
| M | 0° | 8° | 0° | 8° | |



SOLDERING FOOTPRINT



GENERIC MARKING DIAGRAM*



= Assembly Location

= Wafer Lot = Year

= Work Week

= Pb-Free Package (Note: Microdot may be in either location)

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■",

may or may not be present.

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